

Schottky barrier (double) diodes**BAT54W series****FEATURES**

- Low forward voltage
- Guard ring protected
- Very small SMD package.

APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Blocking diodes.

DESCRIPTION

Planar Schottky barrier diodes encapsulated in a SOT323 very small plastic SMD package. Single diodes and double diodes with different pinning are available.

MARKING

TYPE NUMBER	MARKING CODE
BAT54W	L4
BAT54AW	42
BAT54CW	43
BAT54SW	44

PINNING

PIN	BAT54			
	W	AW	CW	SW
1	a	k ₁	a ₁	a ₁
2	n.c.	k ₂	a ₂	k ₂
3	k	a ₁ , a ₂	k ₁ , k ₂	k ₁ , a ₂

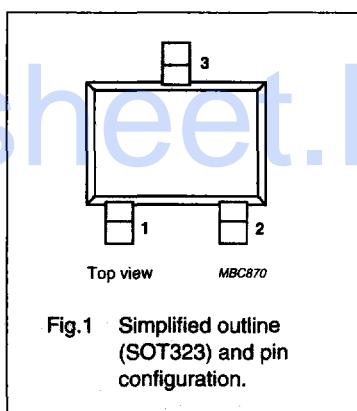


Fig.1 Simplified outline (SOT323) and pin configuration.

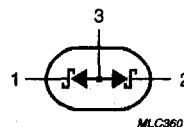


Fig.3 BAT54AW diode configuration (symbol).

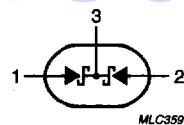


Fig.4 BAT54CW diode configuration (symbol).

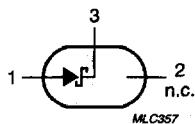


Fig.2 BAT54W single diode configuration (symbol).

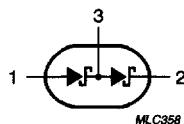


Fig.5 BAT54SW diode configuration (symbol).

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V_R	continuous reverse voltage		-	30	V
I_F	continuous forward current		-	200	mA
I_{FRM}	repetitive peak forward current	$t_p \leq 1 \text{ s}; \delta \leq 0.5$	-	300	mA
I_{FSM}	non-repetitive peak forward current	$t_p < 10 \text{ ms}$	-	600	mA
P_{tot}	total power dissipation (per package)	$T_{amb} \leq 25^\circ\text{C}$	-	200	mW
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		-	125	°C
T_{amb}	operating ambient temperature		-65	+125	°C

ELECTRICAL CHARACTERISTICS

$T_{amb} = 25^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
Per diode				
V_F	forward voltage	see Fig.5 $I_F = 0.1 \text{ mA}$ $I_F = 1 \text{ mA}$ $I_F = 10 \text{ mA}$ $I_F = 30 \text{ mA}$ $I_F = 100 \text{ mA}$	240 320 400 500 800	mV
I_R	reverse current	$V_R = 25 \text{ V}$; note 1; see Fig.6	2	μA
t_{rr}	reverse recovery time	when switched from $I_F = 10 \text{ mA}$ to $I_R = 10 \text{ mA}$; $R_L = 100 \Omega$; measured at $I_R = 1 \text{ mA}$; see Fig.9	5	ns
C_d	diode capacitance	$f = 1 \text{ MHz}$; $V_R = 1 \text{ V}$; see Fig.8	10	pF

Note

1. Pulsed test: $t_p = 300 \mu\text{s}$; $\delta = 0.02$.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R_{thj-a}	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Refer to SOT323 standard mounting conditions.

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GRAPHICAL DATA

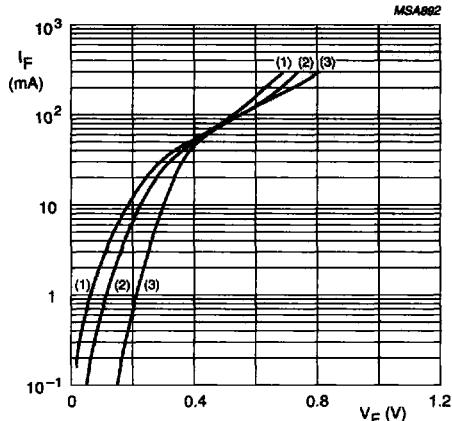


Fig.5 Forward current as a function of forward voltage; typical values.

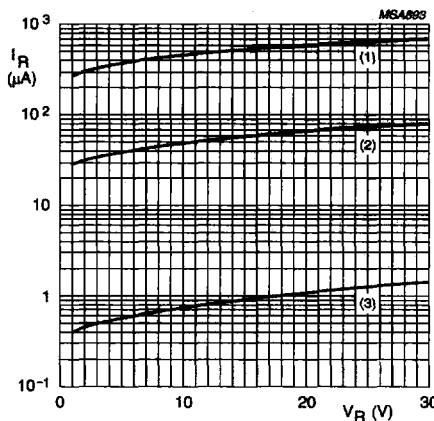


Fig.6 Reverse current as a function of reverse voltage; typical values.

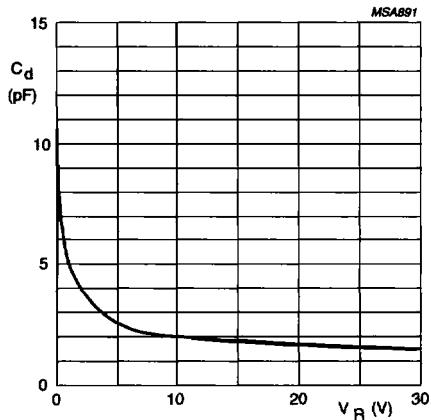


Fig.8 Diode capacitance as a function of reverse voltage; typical values.

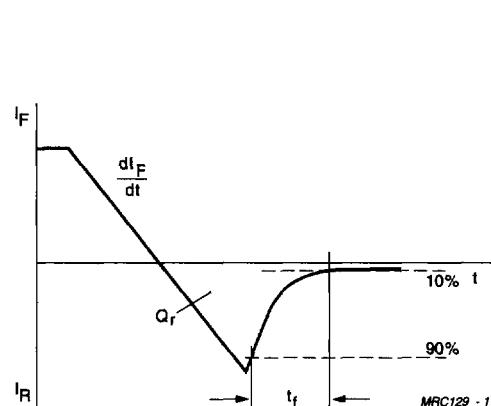


Fig.9 Reverse recovery definitions.